IN THE CLAIMS

Please amend the claims as follows:

Claim 1 (Currently Amended): A complementary field effect transistor comprising:

semiconductor substrate;

an n-type field effect transistor provided on the semiconductor substrate having:

a first gate insulating film containing an oxide including an element selected from the group consisting of group IV metals and Lanthanoid metals, and further containing a compound of the element and boron ~~a group III element except aluminum~~;

a first gate electrode provided on the first gate insulating film; and

n-type source and drain regions formed on both sides of the first gate electrode; and

a p-type field effect transistor provided on the semiconductor substrate having:

a second gate insulating film containing an oxide including an element selected from the group consisting of group IV metals and Lanthanoid metals, and substantially containing no boron ~~none of group III element except aluminum~~;

a second gate electrode provided on the second gate insulating film; and

p-type source and drain regions provided on both sides of the second gate electrode.

Claim 2 (Original): The complementary field effect transistor according to claim 1, wherein a main component of the first gate electrode and a main component of the second gate electrode are the same.

Claim 3 (Original): The complementary field effect transistor according to claim 1, wherein the first and the second gate electrodes consist of one of Mo, Co, Ni, Pt, Cu, Pd, W, PtSi, Pd_2Si and NiSi, or an alloy including one of Mo, Co, Ni, Pt, Cu, Pd, and W.

Claim 4 (Original): The complementary field effect transistor according to claim 1, wherein a concentration of the compound in the first gate insulating film is higher on a side of the first gate electrode than on a side of the semiconductor substrate.

Claim 5 (Original): The complementary field effect transistor according to claim 1, wherein the first gate insulating film includes positive charge.

Claim 6 (Original): The complementary field effect transistor according to claim 5, wherein a concentration of the positive charge in the first gate insulating film is higher on a side of the first gate electrode than on a side of the semiconductor substrate.

Claim 7 (Currently Amended): The complementary field effect transistor according to claim 1, wherein the first gate electrode includes boron ~~the group III element~~.

Claim 8 (Currently Amended): A complementary field effect transistor comprising:

a semiconductor substrate;

an n-type field effect transistor provided on the semiconductor substrate having:

a first gate insulating film containing an oxide including an element selected from the group consisting of group IV metals and Lanthanoid metals, and substantially containing no arsenic ~~none of group V elements and aluminum~~;

a first gate electrode provided on the first gate insulating film; and

n-type source and drain regions formed on both sides of the first gate electrode; and

a p-type field effect transistor provided on the semiconductor substrate having:

a second gate insulating film containing an oxide including an element selected from the group consisting of group IV metals and Lanthanoid metals, and

further containing a compound of the element and arsenic ~~a group V element or aluminum~~;

a second gate electrode provided on the second gate insulating film; and

p-type source and drain regions provided on both sides of the second gate electrode.

Claim 9 (Original): The complementary field effect transistor according to claim 8, wherein a main component of the first gate electrode and a main component of the second gate electrode are the same.

Claim 10 (Original): The complementary field effect transistor according to claim 8, wherein the first and the second gate electrodes consist of one of Mo, Co, Ni, Pt, Cu, Pd, W, PtSi, Pd_2Si and NiSi, or an alloy including one of Mo, Co, Ni, Pt, Cu, Pd, and W.

Claim 11 (Original): The complementary field effect transistor according to claim 8, wherein a concentration of the compound in the second gate insulating film is higher on a side of the first gate electrode than on a side of the semiconductor substrate.

Claim 12 (Original): The complementary field effect transistor according to claim 8, wherein the second gate insulating film includes negative charge.

Claim 13 (Original): The complementary field effect transistor according to claim 12, wherein a concentration of the negative charge in the second gate insulating film is higher on a side of the second gate electrode than on a side of the semiconductor substrate.

Claim 14 (Currently Amended): The complementary field effect transistor according to claim 8, wherein the second gate electrode includes arsenic ~~the group V element or aluminum~~.

Claim 15 (Withdrawn): A manufacturing method of complementary field effect transistor comprising:

forming an oxide film to be made into gate insulating films including an element selected from the group consisting of group IV metals and Lanthanoid metals on regions for an n-type field effect transistor and a p-type field effect transistor on a semiconductor substrate;

forming a metal film to be made into gate electrodes of the n-type field effect transistor and the p-type field effect transistor on the oxide film; and

introducing group III element except aluminum into the oxide film of the region for the n-type field effect transistor selectively.

Claim 16 (Withdrawn): The manufacturing method of complementary field effect transistor according to claim 15, wherein the metal film consists of one of Mo, Co, Ni, Pt, Cu, Pd, W, PtSi, Pd_2Si and NiSi, or an alloy including one of Mo, Co, Ni, Pt, Cu, Pd, and W.

Claim 17 (Withdrawn): The manufacturing method of complementary field effect transistor according to claim 15, wherein the group III element is introduced on a side of the metal film in the oxide film.

Claim 18 (Withdrawn): A manufacturing method of complementary field effect transistor comprising:

forming an oxide film to be made into gate insulating films including an element selected from the group consisting of group IV metals and Lanthanoid metals on regions for an n-type field effect transistor and a p-type field effect transistor on a semiconductor substrate;

forming a metal film to be made into gate electrodes of the n-type field effect transistor and the p-type field effect transistor on the oxide film; and introducing at least one of group V elements and aluminum into the oxide film of the region for the p-type field effect transistor selectively.

Claim 19 (Withdrawn): The manufacturing method of complementary field effect transistor according to claim 18, wherein the metal film consists of one of Mo, Co, Ni, Pt, Cu, Pd, W, PtSi, Pd_2Si and NiSi, or an alloy including one of Mo, Co, Ni, Pt, Cu, Pd, and W.

Claim 20 (Withdrawn): The manufacturing method of complementary field effect transistor according to claim 18, wherein the one of group V elements and aluminum is introduced on a side of the metal film in the oxide film.